## NSN 5961-01-242-2882

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view Offilite at https://defobasegroup.com/histi/0301-01-242-2002
Inclosure Material:
Metal
Overall Length:
1.218 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-59
Internal Junction Configuration:
Pnp
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
0.437 inches
Thread Size:
0.190 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 collector to base voltage/static/emitter open and 80.0 collector to emitter voltage/static/base open and 5.5 emitter to base voltage
static, collector open
Current Rating Per Characteristic:
10.00 amperes source cutoff current
Power Rating Per Characteristic:
58.0 watts small-signal input power, common-collector preset
Transfer Ratio:
200.0 static forward current transfer ratio, common-emitter
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:
3 tab, solder lug
Specification Data:
81349-mil-s-19500/535 government specification
Shelf Life:

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N/a

**Unit Of Measure:** 

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Demilitarization:

No

Fiig:

A110a0